



(51) International Patent Classification:

G02B 1/00 (2006.01) H01L 21/314 (2006.01)
H01Q 15/08 (2006.01) B81B 1/00 (2006.01)

(21) International Application Number:

PCT/SG2019/050510

(22) International Filing Date:

14 October 2019 (14.10.2019)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

10201810181P 15 November 2018 (15.11.2018) SG

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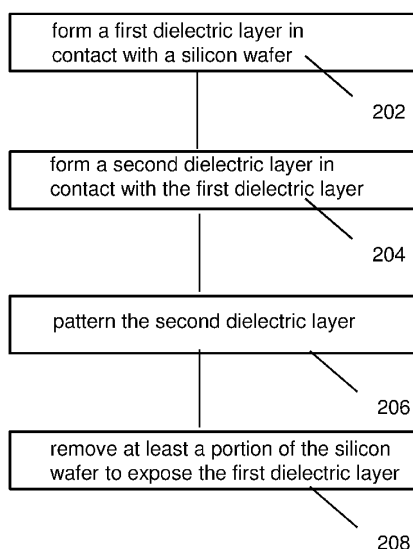
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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH,

(54) Title: META-LENS STRUCTURE AND METHOD OF FABRICATING THE SAME

FIG. 2



(57) Abstract: Various embodiments may provide a method of fabricating a meta-lens structure. The method may include forming a first dielectric layer in contact with a silicon wafer. The method may also include forming a second dielectric layer in contact with the first dielectric layer. A refractive index of the second dielectric layer may be different from a refractive index of the first dielectric layer. The method may further include, in patterning the second dielectric layer. The method may additionally include removing at least a portion of the silicon wafer to expose the first dielectric layer.

GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

- *with international search report (Art. 21(3))*
- *in black and white; the international application as filed contained color or greyscale and is available for download from PATENTSCOPE*